Power Semiconductor Drives By P V Rao

This book provides a survey of the state of the art of technology and future trends in the new family of Smart Power ICs and describes design and applications in a variety of fields ranging from automotive to telecommunications, reliability evaluation and qualification procedures. The book is a valuable source of information and reference for both power IC design specialists and to all those concerned with applications, the development of digital circuits and with system architecture. This book describes the techniques for control of DC and AC motors. It presents a brief introduction of solid state power controltechniques and power semiconductor devices. It also describes firing and commutation circuits, AC to AC voltage control techniques, DC to DC choppers, and DC to AC inverters.

This book covers power electronics, in depth, by presenting the basic principles and application details, which can be used both as a textbook and reference book. Introduces a new method to present power electronics converters called Power Blocks Geometry (PBG) Applicable for courses focusing on power electronics, power electronics converters, and advanced power converters Offers a comprehensive set of simulation results to help understand the

circuits presented throughout the book Power Semiconductor Devices Theory and Applications Vít???zslav Benda Czech Technical University, Prague, Czech Republic John Gowar Duncan A. Grant University of Bristol, UK Recent advances in robotics, automatic control and power conditioning systems have prompted research into increasingly sophisticated power semiconductor devices. This cutting-edge text explores the design, physical processes and applications performance of current power semiconductor devices. The extensive scope covers the complete range of discrete and integrated devices now available. Features include: * Use of physical models to explain the device structures and functions without complicated mathematical techniques * Explanation of the structure, function, characteristics and features of the most important discrete and integrated power devices * Demonstration of the influence of construction and technological parameters on important device characteristics * Sections on power modules and conditions for reliable operation plus a look at future materials and devices This valuable reference encompassing the structure, operation and application of power semiconductor devices will benefit both practising electronics engineers and students of power electronics.

Power electronics is an area of extremely important and rapidly changing technology. Technological Page 2/21

advancements in the area contribute to performance improvement and cost reduction, with applications proliferating in industrial, commercial, residential, military and aerospace environments. This book is meant to help engineers operating in all these areas to stay up-to-date on the most recent advances in the field, as well as to be a vehicle for clarifying increasingly complex theories and mathematics. This book will be a cost-effective and convenient way for engineers to get up-to-speed on the latest trends in power electronics. The reader will obtain the same level of informative instruction as they would if attending an IEEE course or a training session, but without ever leaving the office or living room! The author is in an excellent position to offer this instruction as he teaches many such courses. Selflearning advanced tutorial, falling between a traditional textbook and a professional reference. Almost every page features either a detailed figure or a bulleted chart, accompanied by clear descriptive explanatory text.

Power semiconductor devices are widely used for the control and management of electrical energy. The improving performance of power devices has enabled cost reductions and efficiency increases resulting in lower fossil fuel usage and less environmental pollution. This book provides the first cohesive treatment of the physics and design of silicon carbide power devices with an emphasis on

unipolar structures. It uses the results of extensive numerical simulations to elucidate the operating principles of these important devices. Market_Desc: • Electrical Engineering Students • Electrical Engineering Instructors Power Electronics Engineers Special Features: - Easy to follow step-bystep in depth treatment of all the theory. Computer simulation chapter describes the role of computer simulations in power electronics. Examples and problems based on Pspice and MATLAB are included. Introductory chapter offers a review of basic electrical and magnetic circuit concepts. A new CD-ROM contains the following: Over 100 of new problems of varying degrees of difficulty for homework assignments and self-learning. PSpicebased simulation examples, which illustrate basic concepts and help in design of converters. A newlydeveloped magnetic component design program that demonstrates design trade-offs. PowerPoint-based slides, which will improve the learning experience and the ease of using the book About The Book: The text includes cohesive presentation of power electronics fundamentals for applications and design in the power range of 500 kW or less. It describes a variety of practical and emerging power electronic converters made feasible by the new generation of power semiconductor devices. Topics included in this book are an expanded discussion of diode rectifiers and thyristor converters as well as chapters Page 4/21

on heat sinks, magnetic components which present a step-by-step design approach and a computer simulation of power electronics which introduces numerical techniques and commonly used simulation packages such as PSpice, MATLAB and EMTP. The book summarizes and compares recent advancements in the development of novel lateral power transistors (LDMOS devices) for integrated circuits in power electronic applications. In its first part, the book motivates the necessity for lateral power transistors by a top-down approach: First, it presents typical energy conversion applications in modern industrial, automotive and consumer electronics. Next, it introduces common circuit topologies suitable for these applications, and discusses the feasibility for monolithic integration. Finally, the combination of power and logic functionality on a single chip is motivated and the requirements and limitations for the power semiconductor devices are deduced. The second part describes the evolution of lateral power transistors over the past decades from the simple pin-type concept to double-acting RESURF topologies. It describes the principle of operation for these LDMOS devices and discusses limitations of lateral power devices. Moreover, figures-of-merit are presented which can be used to evaluate the performance of the novel lateral power transistors described in this book with respect to the LDMOS devices. In the last part, [..] the fundamental physical concepts including charge compensation and trench gate topologies are discussed. Also, the status of research in LDMOS devices on silicon carbide is presented. Advantages and drawbacks for each of these integration approaches are summarized, and the feasibility with respect to power electronic applications is evaluated.

This symposium was the sCientific-technical event of the Page 5/21

centennial celebration of the Asea Brown Boveri Switzerland. The purpose was to assess the present state of the art as well as shaping the basis for future progress in the area of power devices and related power circuits. The merger of Brown Boveri (BBC) with Asea to Asea Brown Boveri (ABB) three years ago gave new stimulus and enriched the technical substance of the symposium. By 1991, 100 years after the formation of BBC in Switzerland as a single company, this organization has been decentralized, forming 35 independent ABB companies. One of them - ABB Semiconductors Ltd. - directly deals with the power semiconductor business. These significant changes reflect the changes in the market place: increased competition and higher customer expectations have to be fulfilled. In line with the core business activities of ABB and with the concept of sustainable development, it is natural for ABB to be active in the area of power devices and circuits. Increased awareness towards energy conservation is one of the main drives for these activities. User friendliness is another drive: integration of intelligent functions, e.g. protection and/or increased direct computer interfacing of the power circuits. Therefore, also the R&D activities related to the subject of this symposium will in the future be characterized by an even stronger coupling with the market needs. For the members of the R&D Laboratories this means improved customer partnership beyond operational excellence.

Presents state-of-the-art GaN and SiC electronic devices, as well as detailed applications of these devices to power conditioning, r. f. base station infrastructure and high temperature electronics.

This book provides readers with a variety of tools to address the challenges posed by hot carrier degradation, one of today's most complicated reliability issues in semiconductor devices. Coverage includes an explanation of carrier

transport within devices and book-keeping of how they acquire energy ("become hot"), interaction of an ensemble of colder and hotter carriers with defect precursors, which eventually leads to the creation of a defect, and a description of how these defects interact with the device, degrading its performance.

This clear and concise advanced textbook is a comprehensive introduction to power electronics. The IGBT device has proved to be a highly important Power Semiconductor, providing the basis for adjustable speed motor drives (used in air conditioning and refrigeration and railway locomotives), electronic ignition systems for gasolinepowered motor vehicles and energy-saving compact fluorescent light bulbs. Recent applications include plasma displays (flat-screen TVs) and electric power transmission systems, alternative energy systems and energy storage. This book is the first available to cover the applications of the IGBT, and provide the essential information needed by applications engineers to design new products using the device, in sectors including consumer, industrial, lighting, transportation, medical and renewable energy. The author, B. Jayant Baliga, invented the IGBT in 1980 while working for GE. His book will unlock IGBT for a new generation of engineering applications, making it essential reading for a wide audience of electrical engineers and design engineers, as well as an important publication for semiconductor specialists. Essential design information for applications engineers utilizing IGBTs in the consumer, industrial, lighting, transportation, medical and renewable energy sectors. Readers will learn the methodology for the design of IGBT chips including edge terminations, cell topologies, gate layouts, and integrated current sensors. The first book to cover applications of the IGBT, a device manufactured around the world by more than a dozen companies with sales

exceeding \$5 Billion; written by the inventor of the device. Initially, the only electric loads encountered in an automobile were for lighting and the starter motor. Today, demands on performance, safety, emissions, comfort, convenience, entertainment, and communications have seen the working-in of seemingly innumerable advanced electronic devices. Consequently, vehicle electric systems require larger capacities and more complex configurations to deal with these demands. Covering applications in conventional, hybridelectric, and electric vehicles, the Handbook of Automotive Power Electronics and Motor Drives provides a comprehensive reference for automotive electrical systems. This authoritative handbook features contributions from an outstanding international panel of experts from industry and academia, highlighting existing and emerging technologies. Divided into five parts, the Handbook of Automotive Power Electronics and Motor Drives offers an overview of automotive power systems, discusses semiconductor devices, sensors, and other components, explains different power electronic converters, examines electric machines and associated drives, and details various advanced electrical loads as well as battery technology for automobile applications. As we seek to answer the call for safer, more efficient, and lower-emission vehicles from regulators and consumer insistence on better performance, comfort, and entertainment, the technologies outlined in this book are vital for engineering advanced vehicles that will satisfy these criteria.

Fundamentals of Power Semiconductor Devices provides an in-depth treatment of the physics of operation of power semiconductor devices that are commonly used by the power electronics industry. Analytical models for explaining the operation of all power semiconductor devices are shown. The treatment here focuses on silicon devices but includes the

unique attributes and design requirements for emerging silicon carbide devices. The book will appeal to practicing engineers in the power semiconductor device community. Design, Control and Application of Modular Multilevel Converters for HVDC Transmission Systems is a comprehensive guide to semiconductor technologies applicable for MMC design, component sizing control, modulation, and application of the MMC technology for HVDC transmission. Separated into three distinct parts, the first offers an overview of MMC technology, including information on converter component sizing, Control and Communication, Protection and Fault Management, and Generic Modelling and Simulation. The second covers the applications of MMC in offshore WPP, including planning, technical and economic requirements and optimization options, fault management, dynamic and transient stability. Finally, the third chapter explores the applications of MMC in HVDC transmission and Multi Terminal configurations, including Supergrids. Key features: Unique coverage of the offshore application and optimization of MMC-HVDC schemes for the export of offshore wind energy to the mainland. Comprehensive explanation of MMC application in HVDC and MTDC transmission technology. Detailed description of MMC components, control and modulation, different modeling approaches, converter dynamics under steady-state and fault contingencies including application and housing of MMC in HVDC schemes for onshore and offshore. Analysis of DC fault detection and protection technologies, system studies required for the integration of HVDC terminals to offshore wind power plants, and commissioning procedures for onshore and offshore HVDC terminals. A set of selfexplanatory simulation models for HVDC test cases is available to download from the companion website. This book provides essential reading for graduate students and

researchers, as well as field engineers and professionals who require an in-depth understanding of MMC technology. For some time there has been a need for a semiconductor device book that carries diode and transistor theory beyond an introductory level and yet has space to touch on a wider range of semiconductor device principles and applica tions. Such topics are covered in specialized monographs numbering many hun dreds, but the voluminous nature of this literature limits access for students. This book is the outcome of attempts to develop a broad course on devices and integrated electronics for university students at about senioryear level. The edu cational prerequisites are an introductory course in semiconductor junction and transistor concepts, and a course on analog and digital circuits that has intro duced the concepts of rectification, amplification, oscillators, modulation and logic and SWitching circuits. The book should also be of value to professional engineers and physicists because of both, the information included and the de tailed guide to the literature given by the references. The aim has been to bring some measure of order into the subject area examined and to provide a basic structure from which teachers may develop themes that are of most interest to students and themselves. Semiconductor devices and integrated circuits are reviewed and fundamental factors that control power levels, frequency, speed, size and cost are discussed. The text also briefly mentions how devices are used and presents circuits and comments on representative applications. Thus, the book seeks a balance be tween the extremes of device physics and circuit design. The aim of this book is to provide an overview of the various types of power semiconductor devices, to give an insight into how they function, and to explain and analyze the characteristics of the various components. All the important classes of power semiconductors are covered. Of particular $\frac{Page}{10/21}$

interest, the author takes into account the role of plasma formation in the operation of highpower semiconductor devices.

Less expensive, lighter, and smaller than its electromechanical counterparts, power electronics lie at the very heart of controlling and converting electric energy, which in turn lies at the heart of making that energy useful. From household appliances to space-faring vehicles, the applications of power electronics are virtually limitless. Until now, however, the same could not be said for access to up-todate reference books devoted to power electronics. Written by engineers for engineers. The Power Electronics Handbook covers the full range of relevant topics, from basic principles to cutting-edge applications. Compiled from contributions by an international panel of experts and full of illustrations, this is not a theoretical tome, but a practical and enlightening presentation of the usefulness and variety of technologies that encompass the field. For modern and emerging applications, power electronic devices and systems must be small, efficient, lightweight, controllable, reliable, and economical. The Power Electronics Handbook is your key to understanding those devices, incorporating them into controllable circuits, and implementing those systems into applications from virtually every area of electrical engineering. This symposium provides a forum for technical discussion in areas of power semiconductor devices and power ICs and their applications. It looks at materials and processes; CAD / simulation; devices; high voltage / power ICs; modules and packaging; and applications and measurements. Provides insight on both classical means and new trends in the application of power electronic and artificial intelligence techniques in power system operation and control This book presents advanced solutions for power system controllability improvement, transmission capability enhancement and

operation planning. The book is organized into three parts. The first part describes the CSC-HVDC and VSC-HVDC technologies, the second part presents the FACTS devices. and the third part refers to the artificial intelligence techniques. All technologies and tools approached in this book are essential for power system development to comply with the smart grid requirements. Discusses detailed operating principles and diagrams, theory of modeling, control strategies and physical installations around the world of HVDC and FACTS systems Covers a wide range of Artificial Intelligence techniques that are successfully applied for many power system problems, from planning and monitoring to operation and control Each chapter is carefully edited, with drawings and illustrations that helps the reader to easily understand the principles of operation or application Advanced Solutions in Power Systems: HVDC, FACTS, and Artificial Intelligence is written for graduate students, researchers in transmission and distribution networks, and power system operation. This book also serves as a reference for professional software developers and practicing engineers.

This volume covers five emerging areas of advanced device technology: wide band gap devices, terahertz and millimeter waves, nanometer silicon and silicongermanium devices, nanoelectronics and ballistic devices, and the characterization of advanced photonic and electronic devices. The papers by leading researchers in high speed and advanced electronic and photonic technology presented many firsts and breakthrough results, as has become a tradition with the Lester Eastman Conference, and will allow readers to obtain up-to-date information

about emerging trends and future directions of these technologies. Key papers in each section present snap-shot and mini reviews of state-of-the-art and hot off the press results making the book required reading for engineers, scientists, and students working on advanced and high speed device technology.

The new edition of the most detailed and comprehensive single-volume reference on major semiconductor devices The Fourth Edition of Physics of Semiconductor Devices remains the standard reference work on the fundamental physics and operational characteristics of all major bipolar, unipolar, special microwave, and optoelectronic devices. This fully updated and expanded edition includes approximately 1,000 references to original research papers and review articles, more than 650 high-quality technical illustrations, and over two dozen tables of material parameters. Divided into five parts, the text first provides a summary of semiconductor properties, covering energy band, carrier concentration, and transport properties. The second part surveys the basic building blocks of semiconductor devices, including p-n junctions, metal-semiconductor contacts, and metal-insulatorsemiconductor (MIS) capacitors. Part III examines bipolar transistors, MOSFETs (MOS field-effect transistors), and other field-effect transistors such as JFETs (junction field-effect-transistors) and Page 13/21

MESFETs (metal-semiconductor field-effect transistors). Part IV focuses on negative-resistance and power devices. The book concludes with coverage of photonic devices and sensors, including light-emitting diodes (LEDs), solar cells, and various photodetectors and semiconductor sensors. This classic volume, the standard textbook and reference in the field of semiconductor devices: Provides the practical foundation necessary for understanding the devices currently in use and evaluating the performance and limitations of future devices Offers completely updated and revised information that reflects advances in device concepts, performance, and application Features discussions of topics of contemporary interest, such as applications of photonic devices that convert optical energy to electric energy Includes numerous problem sets, realworld examples, tables, figures, and illustrations; several useful appendices; and a detailed solutions manual Explores new work on leading-edge technologies such as MODFETs, resonant-tunneling diodes, quantum-cascade lasers, single-electron transistors, real-space-transfer devices, and MOScontrolled thyristors Physics of Semiconductor Devices, Fourth Edition is an indispensable resource for design engineers, research scientists, industrial and electronics engineering managers, and graduate students in the field.

Electrostatic discharge (ESD) failure mechanisms

continue to impact semiconductor components and systems as technologies scale from micro- to nanoelectronics. This book studies electrical overstress, ESD, and latchup from a failure analysis and casestudy approach. It provides a clear insight into the physics of failure from a generalist perspective, followed by investigation of failure mechanisms in specific technologies, circuits, and systems. The book is unique in covering both the failure mechanism and the practical solutions to fix the problem from either a technology or circuit methodology. Look inside for extensive coverage on: failure analysis tools, EOS and ESD failure sources and failure models of semiconductor technology, and how to use failure analysis to design more robust semiconductor components and systems; electrothermal models and technologies; the state-of-the-art technologies discussed include CMOS, BiCMOS, silicon on insulator (SOI), bipolar technology, high voltage CMOS (HVCMOS), RF CMOS, smart power, gallium arsenide (GaAs), gallium nitride (GaN), magneto-resistive (MR), giant magneto-resistors (GMR), tunneling magneto-resistor (TMR), devices; micro electro-mechanical (MEM) systems, and photomasks and reticles; practical methods to use failure analysis for the understanding of ESD circuit operation, temperature analysis, power distribution, ground rule development, internal bus distribution, current path analysis, quality metrics, (connecting

the theoretical to the practical analysis); the failure of each key element of a technology from passives, active elements to the circuit, sub-system to package, highlighted by case studies of the elements, circuits and system-on-chip (SOC) in today's products. ESD: Failure Mechanisms and Models is a continuation of the author's series of books on ESD protection. It is an essential reference and a useful insight into the issues that confront modern technology as we enter the Nano-electronic era.

During the last decade many new concepts have been proposed for improving the performance of power MOSFETs. The results of this research are dispersed in the technical literature among journal articles and abstracts of conferences. Consequently, the information is not readily available to researchers and practicing engineers in the power device community. There is no cohesive treatment of the ideas to provide an assessment of the relative merits of the ideas. "Advanced Power MOSFET Concepts" provides an in-depth treatment of the physics of operation of advanced power MOSFETs. Analytical models for explaining the operation of all the advanced power MOSFETs will be developed. The results of numerical simulations will be provided to give additional insight into the device physics and validate the analytical models. The results of twodimensional simulations will be provided to Page 16/21

corroborate the analytical models and give greater insight into the device operation.

Provides the latest techniques and energy-saving applications for working with power semiconductor devices, ac-dc converters, ac-ac converters, dc-dc converters, dc-ac converters. PWM methods, and converter applications. This book starts with a very comprehensive tutorial section which reviews state-of-the-art power electronics technology, integrating power semiconductor devices, different classes of converter topologies, PWM techniques, and key power electronics applications.

Fundamentals of Power Semiconductor DevicesSpringer

From power electronics to power integrated circuits (PICs), smart power technologies, devices, and beyond, Integrated Power Devices and TCAD Simulation provides a complete picture of the power management and semiconductor industry. An essential reference for power device engineering students and professionals, the book not only describes the physics inside integrated power semiconductor devices such lateral double-diffused metal oxide semiconductor field-effect transistors (LDMOSFETs), lateral insulated-gate bipolar transistors (LIGBTs), and super junction LDMOSFETs but also delivers a simple introduction to power management systems. Instead of abstract theoretical treatments and daunting equations, the Page 17/21

text uses technology computer-aided design (TCAD) simulation examples to explain the design of integrated power semiconductor devices. It also explores next generation power devices such as gallium nitride power high electron mobility transistors (GaN power HEMTs). Including a virtual process flow for smart PIC technology as well as a hard-to-find technology development organization chart, Integrated Power Devices and TCAD Simulation gives students and junior engineers a head start in the field of power semiconductor devices while helping to fill the gap between power device engineering and power management systems.

Power semiconductor devices are widely used for the control and management of electrical energy. The improving performance of power devices has enabled cost reductions and efficiency increases resulting in lower fossil fuel usage and less environmental pollution. This book provides the first cohesive treatment of the physics and design of silicon carbide power devices with an emphasis on unipolar structures. It uses the results of extensive numerical simulations to elucidate the operating principles of these important devices. Sample Chapter(s). Chapter 1: Introduction (72 KB). Contents: Material Properties and Technology; Breakdown Voltage; PiN Rectifiers; Schottky Rectifiers; Shielded Schottky Rectifiers; Metal-

Semiconductor Field Effect Transistors; The Baliga-Pair Configuration; Planar Power MOSFETs; Shielded Planar MOSFETs; Trench-Gate Power MOSFETs; Shielded Trendch-Gate MOSFETs; Charge Coupled Structures; Integral Diodes; Lateral High Voltage FETs; Synopsis. Readership: For practising engineers working on power devices, and as a supplementary textbook for a graduate level course on power devices.

A comprehensive, up-to-date and lucidly written book meeting with the long-felt need for a complete text for undergraduate and postgraduate courses. The book is mainly concerned with detailed analysis and design of converters, inverters and power control circuits using solid-state devices. It covers the various types of transformation of energy and discusses the circuits and equipment basic to most electronic devices in use today. With its wide coverage and detailed analysis, is an ideal text for undergraduate and postgraduate and students of electrical engineering and electronics. It would also be highly useful to practicing engineers in the field of power control.

Power Conversion of Renewable Energy Systems presents an introduction to conventional energy conversion components and systems, as well as those related to renewable energy. This volume introduces systems first, and then in subsequent chapters describes the components of energy

systems in detail. Readers will find examples of renewable and conventional energy and power systems, including energy conversion, variable-speed drives and power electronics, in addition to magnetic devices such as transformers and rotating machines. Applications of PSpice, MATLAB, and Mathematica are also included, along with solutions to over 100 application examples. Power Conversion of Renewable Energy Systems aims to instruct readers how to actively apply the theories discussed within. It would be an ideal volume for researchers, students and engineers working with energy systems and renewable energy.

Power electronics, which is a rapidly growing area in terms of research and applications, uses modern electronics technology to convert electric power from one form to another, such as ac-dc, dc-dc, dc-ac, and ac-ac with a variable output magnitude and frequency. Power electronics has many applications in our every day life such as air-conditioners, electric cars, sub-way trains, motor drives, renewable energy sources and power supplies for computers. This book covers all aspects of switching devices, converter circuit topologies, control techniques, analytical methods and some examples of their applications. * 25% new content * Reorganized and revised into 8 sections comprising 43 chapters * Coverage of numerous applications, including uninterruptable power supplies and automotive Page 20/21

electrical systems * New content in power generation and distribution, including solar power, fuel cells, wind turbines, and flexible transmission This book relates the recent developments in several key electrical engineering R&D labs, concentrating on power electronics switches and their use. The first sections deal with key power electronics technologies, MOSFETs and IGBTs, including series and parallel associations. The next section examines silicon carbide and its potentiality for power electronics applications and its present limitations. Then, a dedicated section presents the capacitors, key passive components in power electronics, followed by a modeling method allowing the stray inductances computation, necessary for the precise simulation of switching waveforms. Thermal behavior associated with power switches follows, and the last part proposes some interesting prospectives associated to Power Electronics integration. Copyright: e495f4b5ed12e1844606393d7517f388